



#### **DUAL 20V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BVDSS	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
001/	$25m\Omega$ @ $V_{GS} = 4.5V$	6.0A
20V	31mΩ @ V <sub>GS</sub> = 2.5V	5.1A

## **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Battery Management Application
- Power Management Functions
- DC-DC Converters

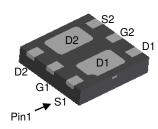
#### **Features**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

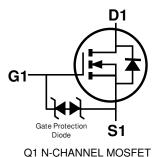
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

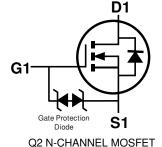




U-DFN2020-6 (Type B)

**Bottom View** 





Internal Schematic

### Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN2025UFDB-7	U-DFN2020-6 (Type B)	3000/Tape & Reel		
DMN2025UFDB-13	U-DFN2020-6 (Type B)	10000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



## **Marking Information**

Site 1



O5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Е		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



O5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Kev

Date Code Key												
Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7		0	1	2	3	4	5	6	7	8	9
Week		1-	·26			27-	·52			5	3	
Code		Α	-Z			a	-Z			7	7	
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	٧	٧	Χ		Υ		Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage			$V_{GSS}$	±10	V
Continuous Drain Current (Note 6) VGS = 4.5V	lo	6.0 4.8	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	5)		I <sub>DM</sub>	35	Α
Continuous Source-Drain Diode Current	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	las	12	Α		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

## **Thermal Characteristics**

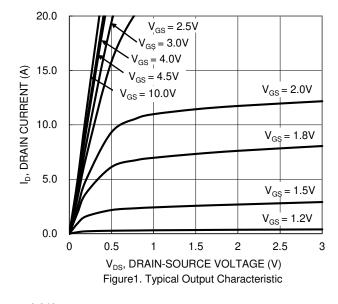
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	170	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	98	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	22		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	- <b>,</b>		- 71		-	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance			18.5	25	mΩ	$V_{GS} = 4.5V, I_{D} = 4A$	
Static Dialif-Source Off-Nesistance	RDS(ON)		26	31	11122	$V_{GS} = 2.5V, I_{D} = 4A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V$ , $I_{S} = 5A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	486	_		V 40V V 0V	
Output Capacitance	Coss	_	92	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	77	_		1 = 1.0101112	
Gate Resistance	Rg	_	3.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	5.9	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	12.3	_	nC	Vps = 10V, lp = 6.5A	
Gate-Source Charge	Qgs	_	0.8	_	110	VDS = 10V, ID = 6.5A	
Gate-Drain Charge	Qgd	_	2.2	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4	_			
Turn-On Rise Time	tr	_	5.4	_	20	$V_{DS} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	tD(OFF)	_	17.6	_	ns	$R_G=6\Omega,~R_L=10\Omega,~I_D=1A$	
Turn-Off Fall Time	tF	_	9.3	_			
Reverse Recovery Time	t <sub>RR</sub>	_	7.7	_	ns	I <sub>F</sub> = 1A, di/dt = 100A/μs	
Reverse Recovery Charge	Q <sub>RR</sub>		1.5	_	nC	$I_F = 1A$ , $di/dt = 100A/\mu s$	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
    Short duration pulse test used to minimize self-heating effect.
    Guaranteed by design. Not subject to product testing.





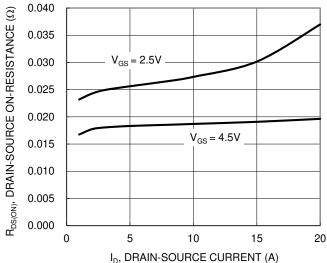


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

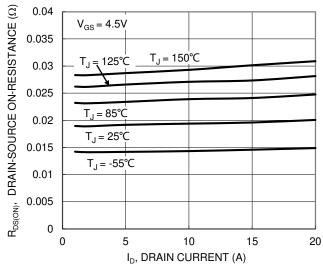


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

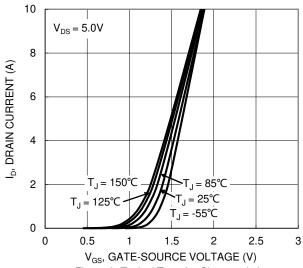


Figure 2. Typical Transfer Characteristic

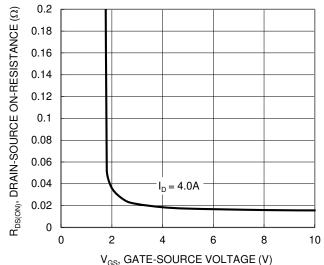


Figure 4. Typical Transfer Characteristic

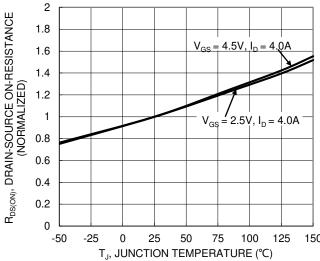


Figure 6. On-Resistance Variation with Temperature



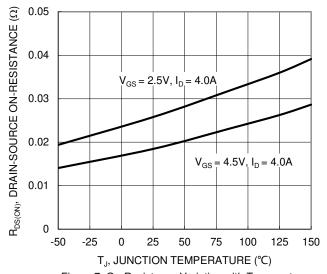


Figure 7. On-Resistance Variation with Temperature

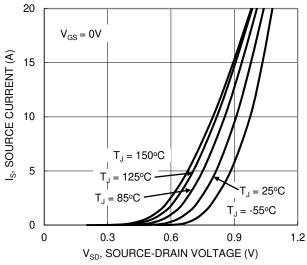
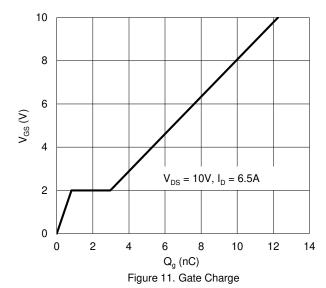
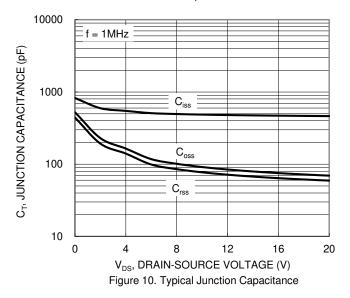


Figure 9. Diode Forward Voltage vs. Current



1.2  $V_{GS(TH)},$  GATE THRESHOLD VOLTAGE (V) 0.9  $I_D = 1mA$ 0.6  $I_{D} = 250 \mu A$ 0.3 0 125 -50 -25 25 50 75 100 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature



100  $R_{\text{DS}(\text{ON})}$  Limited  $P_W = 10ms$ 10 DRAIN CURRENT (A)  $T_{J(Max)} = 150^{\circ}C$   $T_C = 25^{\circ}C$ Single Pulse DUT on 1\*MRP Board  $V_{GS} = 10V$ DC 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



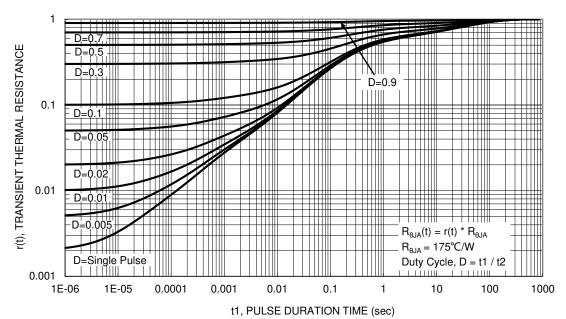


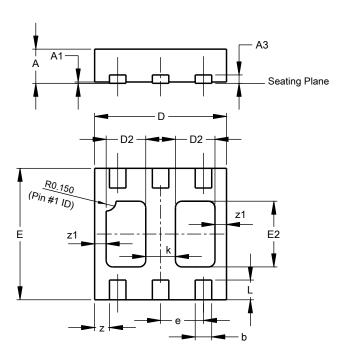
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)

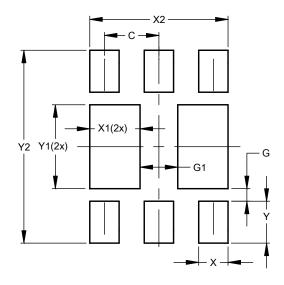


U-DFN2020-6 Type B								
Dim	Min							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
А3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All	Dimens	ions in	mm					

# **Suggested Pad Layout**

 $Please see \ http://www.diodes.com/package-outlines.html \ for the \ latest \ version.$ 

### U-DFN2020-6 (Type B)



Dimensions	Value
Dillicisions	(in mm)
C	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Υ	0.500
Y1	1.000
Y2	2.300



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